

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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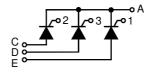


Three Thyristor Module

 $I_{FAV} = 3x 28 A$ $V_{BBM} = 800-1600 V$

Preliminary data

V _{RSM}	V _{RRM} V _{DRM}	Туре
٧	V	
800	800	VYK 70-08io7
1200	1200	VYK 70-12io7
1400	1400	VYK 70-14io7
1600	1600	VYK 70-16io7





Symbol	Test Conditions		Maximum Ratings		
FAVM	T _C = 85°C, 50 - 400 T _C = 85°C, 50 - 400		28 43	A A	
I _{TSM}	$T_{VJ} = 45^{\circ}C;$ $V_{R} = 0$	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	550 600	A A	
		t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	500 550	A A	
∫i²dt	$T_{VJ} = 45^{\circ}C$ $V_{R} = 0$	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	1520 1520	A ² s A ² s	
		t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	1250 1250	A ² s A ² s	
(di/dt) _{cr}	$T_{VJ} = T_{VJM}$ $f = 50 \text{ Hz}, t_p = 200 \text{ µ}$	repetitive, $I_T = 25 \text{ A}$	150	A/μs	
	$V_D = 2/3 V_{DRM}$ $I_G = 0.45 A$ $di_G/dt = 0.45 A/\mu s$	non repetitive, $I_T = I_{TAVM}$	500	A/μs	
(dv/dt) _{cr}	$T_{VJ} = T_{VJM}$; $V_{DR} = 2/3 V_{DRM}$ $R_{GK} = \infty$; method 1 (linear voltage rise)		1000	V/µs	
$\overline{\mathbf{P}_{GM}}$	$T_{VJ} = T_{VJM}$	t _p = 30 μs	10	W	
	$I_{T} = I_{TAVM}$	$t_{p} = 300 \ \mu s$	5	W	
\mathbf{P}_{GAVM}			0.5	W	
V _{RGM}			10	V	
			-40+125	°C	
T _{VJM}			125	°C	
T _{stg}			-40+125	°C	
V _{ISOL}	50/60 Hz, RMS	t = 1 min	2500	V~	
	$I_{ISOL} \le 1 \text{ mA}$	t = 1 s	3000	V~	
M _d	Mounting torque (M5)		5±15 %	Nm	
•		(10-32 UNF)	44±15 %	lb.in.	
Weight	typ.		110	g	

Features

- Package with metal base plate
- Isolation voltage 3000 V~
- Planar passivated chips
- UL applied
- 1/4" fast-on power terminals

Applications

- Switching and control of three phase AC circuits
- Softstart AC motor controller
- · Solid state switches
- · Light and temperature control

Advantages

- Easy to mount with two screws
- · Space and weight savings
- Improved temperature and power cycling

Data according to IEC 60747 refer to a single diode/thyristor unless otherwise stated IXYS reserves the right to change limits, test conditions and dimensions.



Symbol	ool Test Conditions Cl		haracteristic Values		
I _D , I _R	$T_{VJ} = T_{VJM}; V_{R} = V_{RRM}; V_{D} = V_{DRM}$	≤	5	mA	
$\overline{\mathbf{V}_{T}}$	I _T = 45 A; T _{VJ} = 25°C	≤	1.45	V	
V _{T0}	For power-loss calculations only $(T_{VJ} = 125^{\circ}C)$		0.85 11	V mΩ	
V _{GT}	$V_{D} = 6 \text{ V};$ $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = -40^{\circ}\text{C}$ $V_{D} = 6 \text{ V};$ $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = -40^{\circ}\text{C}$	\le \	1.5 1.6 100 200	V V mA mA	
V _{GD}	$T_{VJ} = T_{VJM};$ $V_D = 2/3 V_{DRM}$	<u> </u>	0.2	V mA	
I _L	$T_{VJ} = 25^{\circ}C$; $t_{p} = 10 \mu s$ $I_{G} = 0.45 A$; $di_{G}/dt = 0.45 A/\mu s$	≤	450	mA	
I _H	$T_{VJ} = 25^{\circ}C; V_{D} = 6 V; R_{GK} = \infty$	≤	200	mA	
t _{gd}	$T_{VJ} = 25^{\circ}C; V_{D} = 1/2 V_{DRM}$ $I_{G} = 0.45 A; di_{G}/dt = 0.45 A/\mu s$	≤	2	μS	
t _q	$T_{VJ} = T_{VJM}; I_T = 20 \text{ A}, t_P = 200 \mu\text{s}; di/dt = -10 \text{ A}/\mu\text{s}; V_R = 100 \text{ V}; dv/dt = 15 \text{ V}/\mu\text{s}; V_D = 2/3 \text{ V}_{DRM}$	s typ.	150	μS	
\mathbf{R}_{thJC} \mathbf{R}_{thJH}	per thyristor; sine 180°el per module per thyristor; sine 180°el per module		0.9 0.15 1.1 0.183	K/W K/W K/W	
d _s d _A a	Creeping distance on surface Creepage distance in air Max. allowable acceleration		16.1 6.0 50	mm mm m/s²	

Dimensions in mm (1 mm = 0.0394")

